

**FEATURES**

- **HIGH POWER**  
P1dB=36.0dBm at 5.65GHz to 8.50GHz
- **HIGH GAIN**  
G1dB=28.0dB at 5.65GHz to 8.50GHz
- **BROAD BAND INTERNALLY MATCHED**
- **HERMETICALLY SEALED PACKAGE**

**ABSOLUTE MAXIMUM RATINGS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-5
Input Power	Pin	dBm	18
Flange Temperature	Tc	°C	-30 to +80
Storage Temperature	Tstg	°C	-65 to +175

**RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )**

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDD= 10V IDDset= 1.9A f = 5.65 to 8.50GHz	dBm	34.5	36.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	25.0	28.0	—
Drain Current	IDD		A	—	2.6	3.0
3 <sup>rd</sup> Order Intermodulation Distortion	IM3	Two-tone test Po=25.5dBm (single carrier level)	dBc	-37	-40	—

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**PACKAGE OUTLINE (7-BA25A)**

